# ACPM-5002-TR1

# Multimode PA - UMTS Band2, LTE Band25 and CDMA PCS 3x3mm Power Amplifier Module with Coupler



# **Data Sheet**

# **Description**

The ACPM-5002-TR1 is a fully matched 10-pin surface mount module developed to support multimode applications including UMTS Band2 (1850-1910MHz) and CDMA PCS band including BC14 (1850-1915MHz). The ACPM-5002-TR1 meets stringent linearity requirements up to 28.6dBm output power for UMTS Rel.99 and 28.0dBm for CDMA. The 3mmx3mm form factor package is self contained, incorporating 50ohm input and output matching networks. The PA also contains internal DC blocking capacitors for RF input and output ports.

The ACPM-5002-TR1 features 5<sup>th</sup> generation of CoolPAM (CoolPAM5) circuit technology which supports 3 power modes – active bypass, mid power and high power modes. The CoolPAM is stage bypass technology enhancing PAE (power added efficiency) at low and medium power range. The active bypass feature is added to CoolPAM5 to enhance the PAE further at low output range and it enables the PA to have exceptionally low quiescent current. It dramatically saves the average power consumption and accordingly extends the talk time of mobiles and prolongs a battery life.

A directional coupler is integrated into the module and both coupling and isolation ports are available externally, supporting daisy chain. The integrated coupler has excellent coupler directivity, which minimizes the coupled output power variation or delivered power variation caused by the load mismatch from the antenna. The coupler directivity, or the output power variation into the mismatched load, is critical to the TRP and SAR performance of the mobile phones in real field operations as well as compliance tests for the system specifications.

The ACPM-5002 has integrated on-chip Vrefand on-module bias switch as the one of the key features of the CoolPAM-5, so an external constant voltage source is not required, eliminating the external LDO regulators and switches from circuit boards of mobile devices. It also makes the PA fully digital-controllable by the Ven pin that simply turns the PA on and off from the digital control logic input from baseband chipsets. All of the digital control input pins

#### **Features**

- Thin Package (0.9mm typ)
- Excellent Linearity
- 3-mode power control with Vbp and Vmode
  - Bypass / Mid Power Mode / High Power Mode
- High Efficiency at max output power
- 10-pin surface mounting package
- Internal 50ohm matching networks for both RF input and output
- Integrated coupler
  - Coupler and Isolation ports for daisy chain
- Lead-free, RoHS compliant, Green

# **Applications**

- UMTS Band2
- LTE Band25
- CDMA PCS(BC1) and BC14

# **Ordering Information**

Part Number	Number of Devices	Container
ACPM-5002-TR1	1000	178mm (7") Tape/Reel
ACPM-5002-BLK	100	Bulk

# **Description (Cont.)**

such as the Ven, Vmode and Vbp are fully CMOS compatible and can operate down to the 1.35V logic. The current consumption by digital control pins is negligible.

The power amplifier is manufactured on an advanced InGaP HBT (hetero-junction Bipolar Transistor) MMIC (microwave monolithic integrated circuit) technology offering state-of-the-art reliability, temperature stability and ruggedness.

# **Absolute Maximum Ratings**

No damage assuming only one parameter is set at limit at a time with all other parameters set at or below nominal value.

Operation of any single parameter outside these conditions with the remaining parameters set at or below nominal values may result in permanent damage.

Description	Min.	Typ.	Max.	Unit
RF Input Power (Pin)		0	10	dBm
DC Supply Voltage (Vcc1, Vcc2)	0	3.4	5.0	V
Enable Voltage (Ven)	0	2.6	3.3	V
Mode Control Voltage (Vmode)	0	2.6	3.3	V
Bypass Control (Vbp)	0	2.6	3.3	V
Storage Temperature (Tstg)	-55	25	+125	°C

# **Recommended Operating Condition**

Description		Min.	Тур.	Max.	Unit
DC Supply Voltage (Vcc1, Vcc2)		3.2	3.4	4.2	V
Enable Voltage (Ven)					
-	Low	0	0	0.5	V
	High	1.35	2.6	3.1	V
Mode Control Voltage (Vmode)					
	Low	0	0	0.5	V
	High	1.35	2.6	3.1	V
Bypass Control Voltage (Vbp)					
	Low	0	0	0.5	V
	High	1.35	2.6	3.1	V
Operating Frequency (fo)					
	UMTS	1850		1910	MHz
	CDMA	1850		1915	MHz
Ambient Temperature (Ta)					
	UMTS	-20	25	85	°C
	CDMA	-30	25	85	°C

# **Operating Logic Table**

Power Mode	Ven	Vmode	Vbp	Pout (Rel99)	Pout (HSDPA, HSUPA MPR=0dB)
High Power Mode	High	Low	Χ	~ 28.6 dBm	~ 27.6 dBm
Mid Power Mode	High	High	Low	~ 17 dBm	~ 16 dBm
Bypass Mode	High	High	High	~ 7 dBm	~ 6 dBm
Shut Down Mode	Low	Low	Low	_	_

# **Electrical Characteristics for WCDMA Mode**

- Conditions: Vcc = 3.4V, Ven = 2.6V, Ta = 25°C, Zin/Zout = 50ohm
- Signal Configuration: 3GPP (DPCCH + 1DPDCH) Up-Link unless specified otherwise.

Operating Frequency Range         UMTS (DMA)         1850   - 1910   MHz         MHz           Maximum Output Power (High Power Mode)         Rel99         28.6         1915   MHz         MHz           Maximum Output Power (High Power Mode)         ESDPA, HSUPA MPR=0dB         27.6         180         dBm           Gain         High Power Mode, Pout=28.6dBm         25         28.5         08         dB           Gain         High Power Mode, Pout=28.6dBm         14.5         18.5         08         dB           Power Added Efficiency         High Power Mode, Pout=28.6dBm         36.7         40.1         08         dB           Power Added Efficiency         High Power Mode, Pout=28.6dBm         15.3         20.2         08         08           Power Added Efficiency         High Power Mode, Pout=28.6dBm         15.3         20.2         08         08           Power Added Efficiency         High Power Mode, Pout=28.6dBm         15.3         20.2         08         08         08         08         08         08         08         08         08         08         08         08         08         08         08         08         08	Characteristics		Condition	Min.	Тур.	Max.	Unit
Maximum Output Power Mode   Find Power Mode	Operating Frequency	/ Range			_		
HSDPA, HSUPA MPR=0dB					-	1915	
Migh Power Mode, Pout=28.6dBm   25   28.5   28.5   28.6		ower					
Gain         High Power Mode, Pout=28.6dBm         25         28.5         dB           Mid Power Mode, Pout=17dBm         14.5         18.5         36           Bypas Mode, Pout=27dBm         7         11         36           Power Added Efficies	(High Fower Mode)		·				
Mid Power Mode, Pout=17dBm							
Power Added Efficient   Figure 1   Figure 2   Figure 3   Figure	Gain						
Power Added Efficients			·				
Mid Power Mode, Pout=17dBm			* *	-			
Page	Power Added Efficier	ncy		36.7	40.1		
Total Supply Current Leading Four Properties of Mid Power Mode, Pour Park Mid Power Mode			·	15.3	20.2		%
Mid Power Mode, Pout=17dBm			Bypass Mode, Pout=7dBm	6.8	12.3		%
Mid Power Mode, Pout=13.5dBm   50 mA   mA   math of the pages Mode, Pout=2,5dBm   11   20 mA   mA   math of the pages Mode, Pout=3,5dBm   8.5 mA   mA   mA   mA   mA   mA   mA   mA	<b>Total Supply Current</b>		High Power Mode, Pout=28.6dBm		530	580	mA
Bypass Mode, Pout=7dBm   11   20 mA			Mid Power Mode, Pout=17dBm		72	95	mA
Power Mode   Power Mode   Res   Power Mode   Res   Res   Power Mode   Res			Mid Power Mode, Pout=13.5dBm		50		mA
High Power Mode         85         117         150         mA           Mid Power Mode         10         20         30         mA           Bopass Mode         1         3.1         5         mA           Enable Current         High Power Mode         5         µA           Brown Mode         5         µA         µA           Mode Control Current         Mid Power Mode         5         µA           Mode Control Current         Mid Power Mode         5         µA           Bypass Mode         5         µA         µA           Bypass Mode         9         5         µA           Bypass Mode         9         9         µA         <			Bypass Mode, Pout=7dBm		11	20	mA
Mid Power Mode   10   20   30   mA     Bypass Mode   1   3.1   5   mA     Finable Current   High Power Mode   5   μA     Mid Power Mode   7   μA     Mid Power Mode			Bypass Mode, Pout=3.5dBm		8.5		mA
Bypass Mode         1         3.1         5         mA           Enable Current         High Power Mode         5         μA           Mid Power Mode         5         μA           Mode Control Current         Mid Power Mode         5         μA           Bypass Mode         5         μA           Bypass Mode         5         μA           Bypass Control Current         Bypass Mode         5         μA           Bypass Mode         5         μA           Bypass Control Current         Pout ≤ (max mode = 0V, Vbp=0V         5         μA           UMTS Adjacent         Pout ≤ (max power – MPR)         41         -36         dBc           UMTS Adjacent Channel         \$1.25 MHz offset         Pout ≤ (max power – MPR)         49         -44         dBc           Leakage Ratio (ACPR)         \$1.25 MHz offset         Pout ≤ max power – MPR)         -58         -53         dBc           LEFACLR         \$1.25 MHz offset         Pout ≤ (maximum power – MPR)         -33         dBc           LEFACLR         \$1.25 MHz offset         Pout ≤ (maximum power – MPR)         -33         dBc           LEFACLR2         Pout ≤ (maximum power – MPR)         -57         -42         dBc <td colspan="2">Quiescent Current</td> <td>High Power Mode</td> <td>85</td> <td>117</td> <td>150</td> <td>mA</td>	Quiescent Current		High Power Mode	85	117	150	mA
High Power Mode         5         μA           Mid Power Mode         5         μA           Bypass Mode         5         μA           Mode Control Current         Mid Power Mode         5         μA           Bypass Mode         5         μA           Bypass Mode         5         μA           Bypass Control Current         Bypass Mode         5         μA           Total Current in Powdown mode         Ven=0V, Vmode=0V, Vbp=0V         5         μA           Channel Channel Shatz offset         5 MHz offset         Pout ≤ (max power – MPR)         -41         -36         dBc           Channel Adjacent Channel Shatz offset         10 MHz offset         Pout ≤ max power         -54         -46         dBc           LE ACLR         -59         -44         dBc           Power Ratio (ACPR) 3 ± 1.98 MHz offset         Pout ≤ max power         -98         -53         dBc           LE ACLR Pout ≤ (maximum power – MPR)         -36         -36         dBc           LE ACLR Pout ≤ (maximum power – MPR)         -36         dBc           LE ACLR Pout ≤ (maximum power – MPR)         -57         -42         dBc <td< td=""><td colspan="2"></td><td>Mid Power Mode</td><td>10</td><td>20</td><td>30</td><td>mA</td></td<>			Mid Power Mode	10	20	30	mA
Mid Power Mode   5			Bypass Mode	1	3.1	5	mA
Mode Control Currest   Mid Power Mode   5	Enable Current		High Power Mode		5		μΑ
Mode Control Currest   Mid Power Mode   5			Mid Power Mode		5		μA
Bypass Mode   5			Bypass Mode		5		
Bypass Mode   5	Mode Control Currer	nt	· ·		5		•
Bypass Control Current in Power-down mode         bypass         5         μA           Total Current in Power-down mode         Ven=0V, Vmode=0V, Vbp=0V         5         μA           UMTS Adjacent           Channel         5 MHz offset         -41         -36         dBc           Channel         5 MHz offset         -41         -36         dBc           Leakage Ratio (ACLR)         10 MHz offset         -54         -46         dBc           Adjacent Channel         ±1.25 MHz offset         Pout ≤ max power         -49         -44         dBc           Power Ratio (ACPR)         ±1.98 MHz offset         -58         -53         dBc           LTE ACLR         LTE to LTE, E-UTRAACLR Pout ≤ (maximum power - MPR)         -33         dBc           UTRAACLR1 Pout ≤ (maximum power - MPR)         -36         dBc           UTRAACLR2 Pout ≤ (maximum power - MPR)         -39         dBc           UTRAACLR2 Pout ≤ (maximum power - MPR)         -57         -42         dBc           Suppression         Third         -57         -42         dBc           Input VSWR         Stability (Spurious Output)         VSWR 5:1, All phase         -60         dBc           Stability (Spurious Output)         VSWR 5:1, All pho			Bypass Mode		5		-
Total Current in Power-down mode         Ven=0V, Vmode=0V, Vbp=0V         5         μA           UMTS Adjacent         Pout ≤ (max power − MPR)           Channel         5 MHz offset         -41         -36         dBc           Leakage Ratio           (ACLR)         10 MHz offset         Pout ≤ max power         -54         -46         dBc           Adjacent Channel         ±1.25 MHz offset         Pout ≤ max power         -49         -44         dBc           Power Ratio (ACPR)         ±1.98 MHz offset         -58         -53         dBc           LTE to LTE, E-UTRAACLR Pout ≤ (maximum power − MPR)         -33         dBc           UTRAACLR1 Pout ≤ (maximum power − MPR)         -36         dBc           UTRAACLR2 Pout ≤ (maximum power − MPR)         -39         dBc           UTRAACLR2 Pout ≤ (maximum power − MPR)         -41         -35         dBc           UTRAACLR2 Pout ≤ (maximum power − MPR)         -57         -42         dBc           UTRAACLR2 Pout ≤ (maximum power − MPR)         -57         -42         dBc           UTRAACLR2 Pout ≤ (maximum power − MPR)         -57         -42         dBc	Bypass Control Curre	nt					•
UMTS Adjacent         Pout ≤ (max power – MPR)           Channel         5 MHz offset         -41         -36         dBc           Leakage Ratio         -54         -46         dBc           Adjacent Channel         ±1.25 MHz offset         Pout ≤ max power         -49         -44         dBc           Power Ratio (ACPR)         ±1.98 MHz offset         LTE to LTE, E-UTRAACLR Pout ≤ (maximum power – MPR)         -33         dBc           LTE ACLR         UTRAACLR1 Pout ≤ (maximum power – MPR)         -36         dBc           LTE ACLR2         UTRAACLR2 Pout ≤ (maximum power – MPR)         -39         dBc           LTE ACLR2         Fout ≤ (maximum power – MPR)         -41         -35         dBc           LTE ACLR3         High Power Mode, Pout=28.6dBm         -41         -35         dBc           LTE ACLR3         Third         -57         -42         dBc           LTE ACLR3         VSWR 5:1, All phase         -60         dBc           LTE ACLR4         VSWR 5:1, All phase         -60         dBm/Hz           LTE ACLR4         High Power Mode, Pout=28.6dBm         -137         dBm/Hz						5	
Channel Leakage Ratio (ACLR)       5 MHz offset       -41       -36       dBc         Adjacent Channel Power Ratio (ACPR)       ±1.25 MHz offset       Pout ≤ max power       -49       -44       dBc         Fower Ratio (ACPR)       ±1.98 MHz offset       Pout ≤ max power       -58       -53       dBc         LTE ACLR       ±1.98 MHz offset       LTE to LTE, E-UTRAACLR Pout ≤ (maximum power - MPR)       -33       dBc         LTE ACLR       UTRAACLR1 Pout ≤ (maximum power - MPR)       -36       dBc         UTRAACLR2 Pout ≤ (maximum power - MPR)       -39       dBc         Harmonic Suppression       Second Third       High Power Mode, Pout=28.6dBm       -41       -35       dBc         Input VSWR       -57       -42       dBc         Stability (Spurious Output)       VSWR 5:1, All phase       -60       dBc         Rx Band Noise Power (Vcc=4.2V)       High Power Mode, Pout=28.6dBm       -137       -38       dBm/Hz         GPS Band Noise Power (Vcc=4.2V)       High Power Mode, Pout=28.6dBm       -137       -36       dBm/Hz			· · · · · · · · · · · · · · · · · · ·				F
(ACLR)         10 MHz offset         Pout ≤ max power         -54         -46         dBc           Adjacent Channel Power Ratio (ACPR)         ±1.98 MHz offset         Pout ≤ max power         -49         -44         dBc           LTE ACLR         ±1.98 MHz offset         Fout ≤ (TRAACLR)         -58         -53         dBc           LTE ACLR         Pout ≤ (maximum power - MPR)         -33         dBc           Harmonic Suppression         Second Third         High Power Mode, Pout=28.6dBm         -41         -35         dBc           Suppression         Third         -57         -42         dBc           Input VSWR         VSWR 5:1, All phase         -60         dBc           Stability (Spurious Output)         VSWR 5:1, All phase         -137         dBm/Hz           GPS Band Noise Power (Vcc=4.2V)         High Power Mode, Pout=28.6dBm         -137         dBm/Hz	Channel	5 MHz offset			-41	-36	dBc
Power Ratio (ACPR) ±1.98 MHz offset         -58         -53         dBc           LTE ACLR         LTE to LTE, E-UTRA <sub>ACLR</sub> Pout ≤ (maximum power – MPR)         -33         dBc           UTRA <sub>ACLR1</sub> Pout ≤ (maximum power – MPR)         -36         dBc           UTRA <sub>ACLR2</sub> Pout ≤ (maximum power – MPR)         -39         dBc           Harmonic Second Third         High Power Mode, Pout=28.6dBm         -41         -35         dBc           Stability (Spurious Output)         VSWR 5:1, All phase         2.5:1         -57         -42         dBc           Stability (Spurious Output)         VSWR 5:1, All phase         -60         dBc           Rx Band Noise Power (Vcc=4.2V)         High Power Mode, Pout=28.6dBm         -137         dBm/Hz           GPS Band Noise Power (Vcc=4.2V)         High Power Mode, Pout=28.6dBm         -138         dBm/Hz	_	10 MHz offset			-54	-46	dBc
	Adjacent Channel	±1.25 MHz offset	Pout ≤ max power		-49	-44	dBc
$Pout \leq (maximum power - MPR) \\ UTRA_{ACLR1} \\ Pout \leq (maximum power - MPR) \\ UTRA_{ACLR2} \\ Pout \leq (maximum power - MPR) \\ Harmonic \\ Suppression \\ Third \\ Suppression \\ Third \\ Stability (Spurious Output) \\ SWR 5:1, All phase \\ GPS Band Noise Power (Vcc=4.2V) \\ High Power Mode, Pout=28.6dBm \\ -137 \\ -35 \\ -39 \\ -39 \\ -39 \\ -41 \\ -35 \\ -35 \\ -35 \\ -42 \\ -35 \\ -3$	Power Ratio (ACPR)	±1.98 MHz offset			-58	-53	
$ Pout \leq (maximum power - MPR) \\ UTRA_{ACLR2} \\ Pout \leq (maximum power - MPR) \\ Harmonic \\ Suppression \\ Third \\ Input VSWR \\ Suppression \\ Third \\ VSWR 5:1, All phase \\ Rx Band Noise Power (Vcc=4.2V) \\ High Power Mode, Pout=28.6dBm \\ -57 \\ -42 \\ -57 \\ -42 \\ -41 \\ -35 \\ -35 \\ -35 \\ -37 \\ -42 \\ -42 \\ -2.5:1 \\ -60 \\ -37 \\ -48 \\ -60 \\ -38 \\ -337 \\ -38 \\ -$	LTE ACLR					-33	dBc
Pout ≤ (maximum power – MPR)  Harmonic Second High Power Mode, Pout=28.6dBm -41 -35 dBc Suppression Third -57 -42 dBc  Input VSWR  Stability (Spurious Output) VSWR 5:1, All phase -60 dBc  Rx Band Noise Power (Vcc=4.2V) High Power Mode, Pout=28.6dBm -137 dBm/Hz  GPS Band Noise Power (Vcc=4.2V) High Power Mode, Pout=28.6dBm -138 dBm/Hz						-36	dBc
SuppressionThird-57-42dBcInput VSWR2.5:1Stability (Spurious Output)VSWR 5:1, All phase-60dBcRx Band Noise Power (Vcc=4.2V)High Power Mode, Pout=28.6dBm-137dBm/HzGPS Band Noise Power (Vcc=4.2V)High Power Mode, Pout=28.6dBm-138dBm/Hz						-39	dBc
Input VSWR 2.5:1  Stability (Spurious Output) VSWR 5:1, All phase -60 dBc  Rx Band Noise Power (Vcc=4.2V) High Power Mode, Pout=28.6dBm -137 dBm/Hz  GPS Band Noise Power (Vcc=4.2V) High Power Mode, Pout=28.6dBm -138 dBm/Hz	Harmonic	Second	High Power Mode, Pout=28.6dBm		-41	-35	dBc
Stability (Spurious Output)  VSWR 5:1, All phase  -60 dBc  Rx Band Noise Power (Vcc=4.2V)  High Power Mode, Pout=28.6dBm  -137 dBm/Hz  GPS Band Noise Power (Vcc=4.2V)  High Power Mode, Pout=28.6dBm  -138 dBm/Hz	Suppression	Third			-57	-42	dBc
Rx Band Noise Power (Vcc=4.2V) High Power Mode, Pout=28.6dBm -137 dBm/Hz GPS Band Noise Power (Vcc=4.2V) High Power Mode, Pout=28.6dBm -138 dBm/Hz	Input VSWR					2.5:1	
GPS Band Noise Power (Vcc=4.2V) High Power Mode, Pout=28.6dBm -138 dBm/Hz	Stability (Spurious O	utput)	VSWR 5:1, All phase			-60	dBc
	Rx Band Noise Power	r (Vcc=4.2V)	High Power Mode, Pout=28.6dBm		-137		dBm/Hz
ISM Band Noise Power (Vcc=4.2V) High Power Mode, Pout=28.6dBm -145 dBm/Hz	GPS Band Noise Pow	er (Vcc=4.2V)	High Power Mode, Pout=28.6dBm		-138		dBm/Hz
	ISM Band Noise Powe	er (Vcc=4.2V)	High Power Mode, Pout=28.6dBm		-145		dBm/Hz

# **Electrical Characteristics for WCDMA Mode (Cont.)**

Rx Band Gain (2110–2170MHz)	Where G is gain in Tx band	G-2	dB
GPS Band Gain (1574-1577MHz)	Where G is gain in Tx band	d G-2.5	
GLONASS Band Gain (1597-1607MHz)	Where G is gain in Tx band	G-1.5	dB
ISM Band Gain (2400-2483.5MHz)	Where G is gain in Tx band	G-12	dB
Media Band Gain (716-728MHz)	Where G is gain in Tx band	G-24	dB
Phase Discontinuity	low power mode↔mid power mode, at Pout=7dBm mid power mode↔high power mode, at Pout=17dBm	20 30	deg deg
Ruggedness	Pout<28.6dBm, Pin<10dBm, All phase High Power Mode	10:1	VSWR
Coupling factor	RF Out to CPL port	20	dB
Daisy Chain Insertion Loss	ISO port to CPL port, Ven=Low	0.25	dB

#### **HSDPA Signal configuration used:**

3GPPTS 34.121-1

Annex C (normative e): Measurement channels

C.10.1 UL reference measurement channel for HSDPA tests

Table C.10.1.4: β values for transmitter characteristics tests with HS-DPCCH

Sub-test 2 (CM=1.0, MPR=0.0)

# **HSUPA signal configuration used:**

3GPPTS 34.121-1

Annex C (normative): Measurement channels

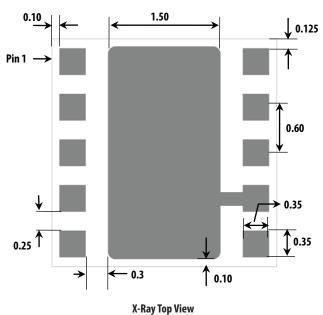
C.11.1 UL reference measurement channel for E-DCH tests

Table C.11.1.3:  $\beta$  values for transmitter characteristics tests with HS-DPCCH and E-DCH Sub-test 1 (CM=1.0, MPR=0.0)

At 3.2V operation, 0.5dB backoff is allowed for maximum power output.

# **Footprint**

All dimensions are in millimeter

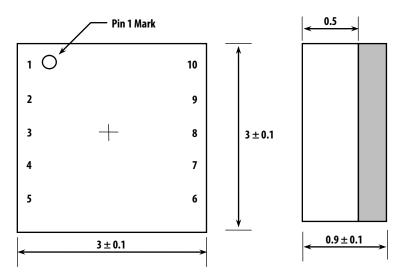


#### **PIN Description**

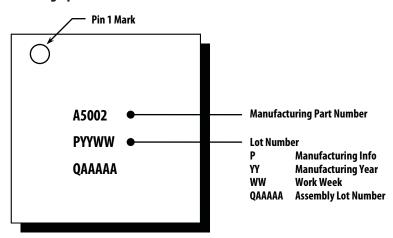
Name	Description
Vcc1	DC Supply Voltage
RFin	RF Input
Vbp	Bypass Control
Vmode	Mode Control
Ven	PA Enable
CPL	Coupling port of Coupler
GND	Ground
ISO	Isolation port of Coupler
RFOut	RF Out
Vcc2	DC Supply Voltage
	Vcc1 RFin Vbp Vmode Ven CPL GND ISO RFOut

# **Package Dimensions**

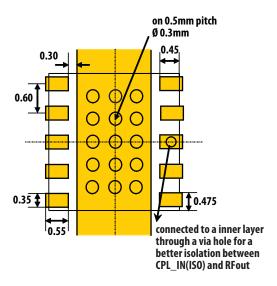
All dimensions ae in millimeter



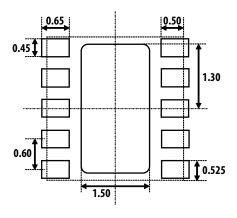
# **Marking Specification**



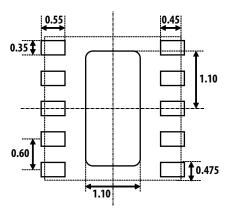
#### Metallization



# **Solder Mask Opening**



# **Solder Paste Stencil Aperture**



# **PCB Design Guidelines**

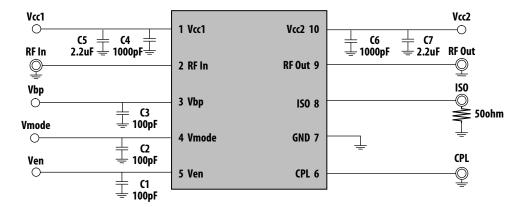
The recommended PCB land pattern is shown in figures on the left side. The substrate is coated with solder mask between the I/O and conductive paddle to protect the gold pads from short circuit that is caused by solder bleeding/bridging.

# **Stencil Design Guidelines**

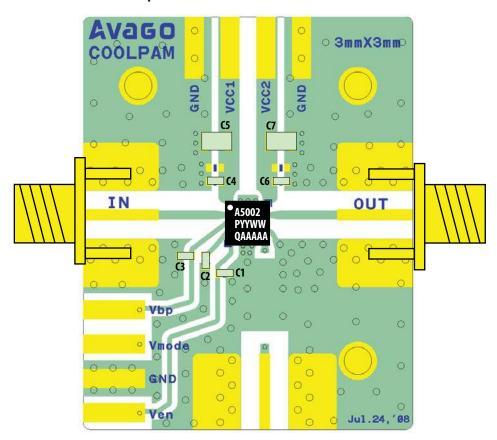
A properly designed solder screen or stencil is required to ensure optimum amount of solder paste is deposited onto the PCB pads.

The recommended stencil layout is shown here. Reducing the stencil opening can potentially generate more voids. On the other hand, stencil openings larger than 100% will lead to excessive solder paste smear or bridging across the I/O pads or conductive paddle to adjacent I/O pads. Considering the fact that solder paste thickness will directly affect the quality of the solder joint, a good choice is to use laser cut stencil composed of 0.100mm(4mils) or 0.127mm(5mils) thick stainless steel which is capable of producing the required fine stencil outline.

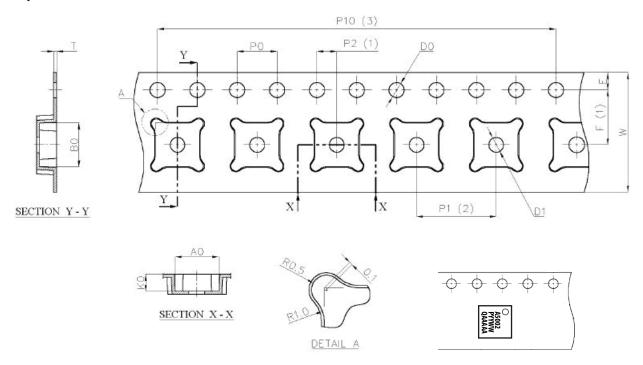
# **Evaluation Board Schematic**



# **Evaluation Board Description**



# **Tape and Reel Information**



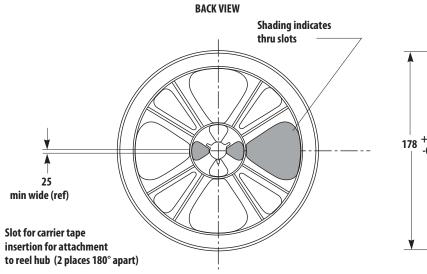
# **Dimension List**

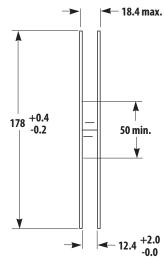
Annote	Millimeter
A0	3.40±0.10
В0	3.40±0.10
K0	1.35±0.10
D0	1.55±0.05
D1	1.60±0.10
P0	4.00±0.10
P1	8.00±0.10

Annote	Millimeter
P2	2.00±0.05
P10	40.00±0.20
Е	1.75±0.10
F	5.50±0.05
W	12.00±0.30
Т	0.30±0.05

Tape and Reel Format – 3 mm x 3 mm

# **Reel Drawing**





# FRONT VIEW 1.5 min. 13.0 ± 0.2 21.0 ± 0.8

Plastic Reel Format (all dimensions are in millimeters)

#### NOTES:

- 1. Reel shall be labeled with the following information (as a minimum).
  - a. manufacturers name or symbol
  - b. Avago Technologies part number
  - c. purchase order number
  - d. date code
  - e. quantity of units
- A certificate of compliance (c of c) shall be issued and accompany each shipment of product.
- 3. Reel must not be made with or contain ozone depleting materials.
- 4. All dimensions in millimeters (mm)

# **Handling and Storage**

#### ESD (Electrostatic Discharge)

Electrostatic discharge occurs naturally in the environment. With the increase in voltage potential, the outlet of neutralization or discharge will be sought. If the acquired discharge route is through a semiconductor device, destructive damage will result.

ESD countermeasure methods should be developed and used to control potential ESD damage during handling in a factory environment at each manufacturing site.

#### **MSL (Moisture Sensitivity Level)**

Plastic encapsulated surface mount package is sensitive to damage induced by absorbed moisture and temperature.

Avago Technologies follows JEDEC Standard J-STD 020B. Each component and package type is classified for moisture sensitivity by soaking a known dry package at

various temperatures and relative humidity, and times. After soak, the components are subjected to three consecutive simulated reflows.

The out of bag exposure time maximum limits are determined by the classification test describe below which corresponds to a MSL classification level 6 to 1 according to the JEDEC standard IPC/JEDEC J-STD-020B and J-STD-033.

ACPM-5002-TR1 is MSL3. Thus, according to the J-STD-033 p.11 the maximum Manufacturers Exposure Time (MET) for this part is 168 hours. After this time period, the part would need to be removed from the reel, de-taped and then re-baked. MSL classification reflow temperature for the ACPM-5002-TR1 is targeted at 260°C+0/-5°C. Figure and table on next page show typical SMT profile for maximum temperature of 260 +0/-5°C.

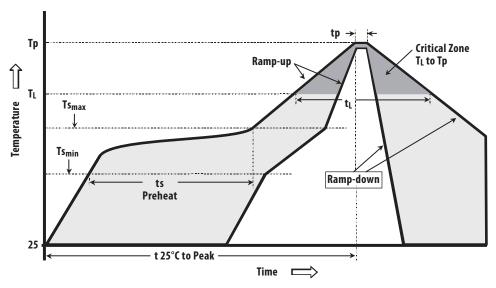
#### **Moisture Classification Level and Floor Life**

MSL Level	Floor Life (out of bag) at factory ambient $=$ < $30^{\circ}$ C/ $60\%$ RH or as stated
1	Unlimited at =< 30°C/85% RH
2	1 year
2a	4 weeks
3	168 hours
4	72 hours
5	48 hours
5a	24 hours
6	Mandatory bake before use. After bake, must be reflowed within the time limit specified on the label

#### Note

<sup>1.</sup> The MSL Level is marked on the MSL Label on each shipping bag.

# **Reflow Profile Recommendations**



Typical SMT Reflow Profile for Maximum Temperature = 260 + 0/-5°C

Typical SMT Reflow Profile for Maximum Temperature = 260 + 0/-5°C

Profile Feature	Sn-Pb Solder	Pb-Free Solder
Average ramp-up rate (TL to TP)	3°C/sec max	3°C/sec max
Preheat		
– Temperature Min (Tsmin)	100°C	150°C
– Temperature Max (Tsmax)	150°C	200°C
– Time (min to max) (ts)	60-120 sec	60-120 sec
Tsmax to TL		
– Ramp-up Rate		3°C/sec max
Time maintained above:		
– Temperature (TL)	183°C	217°C
– Time (TL)	60-150 sec	60-150 sec
Peak temperature (Tp)	240 +0/-5°C	260 +0/-5°C
Time within 5°C of actual Peak Temperature (tp)	10-30 sec	20-40 sec
Ramp-down Rate	6°C/sec max	6°C/sec max
Time 25°C to Peak Temperature	6 min max.	8 min max.

# **Storage Condition**

Packages described in this document must be stored in sealed moisture barrier, antistatic bags. Shelf life in a sealed moisture barrier bag is 12 months at <40°C and 90% relative humidity (RH) J-STD-033 p.7.

# **Out-of-Bag Time Duration**

After unpacking the device must be soldered to the PCB within 168 hours as listed in the J-STD-020B p.11 with factory conditions <30°C and 60% RH.

# **Baking**

It is not necessary to re-bake the part if both conditions (storage conditions and out-of bag conditions) have been satisfied. Baking must be done if at least one of the conditions above have not been satisfied. The baking conditions are 125°C for 12 hours J-STD-033 p.8.

#### **CAUTION**

Tape and reel materials typically cannot be baked at the temperature described above. If out-of-bag exposure time is exceeded, parts must be baked for a longer time at low temperatures, or the parts must be de-reeled, de-taped, re-baked and then put back on tape and reel. (See moisture sensitive warning label on each shipping bag for information of baking).

# Board Rework Component Removal, Rework and Remount

If a component is to be removed from the board, it is recommended that localized heating be used and the maximum body temperatures of any surface mount component on the board not exceed 200°C. This method will minimize moisture related component damage. If any component temperature exceeds 200°C, the board must be baked dry per 4-2 prior to rework and/or component removal. Component temperatures shall be measured at the top center of the package body. Any SMD packages that have not exceeded their floor life can be exposed to a maximum body temperature as high as their specified maximum reflow temperature.

# **Removal for Failure Analysis**

Not following the above requirements may cause moisture/reflow damage that could hinder or completely prevent the determination of the original failure mechanism.

# **Baking of Populated Boards**

Some SMD packages and board materials are not able to withstand long duration bakes at 125°C. Examples of this are some FR-4 materials, which cannot withstand a 24 hr bake at 125°C. Batteries and electrolytic capacitors are also temperature sensitive. With component and board temperature restrictions in mind, choose a bake temperature from Table 4-1 in J-STD 033; then determine the appropriate bake duration based on the component to be removed. For additional considerations see IPC-7711 and IPC-7721.

# **Derating due to Factory Environmental Conditions**

Factory floor life exposures for SMD packages removed from the dry bags will be a function of the ambient environmental conditions. A safe, yet conservative, handling approach is to expose the SMD packages only up to the maximum time limits for each moisture sensitivity level as shown in next table. This approach, however, does not work if the factory humidity or temperature is greater than the testing conditions of 30°C/60% RH. A solution for addressing this problem is to derate the exposure times based on the knowledge of moisture diffusion in the component package materials ref. JESD22-A120). Recommended equivalent total floor life exposures can be estimated for a range of humidities and temperatures based on the nominal plastic thickness for each device.

Table on next page lists equivalent derated floor lives for humidities ranging from 20-90% RH for three temperature, 20°C, 25°C, and 30°C.

Table on next page is applicable to SMDs molded with novolac, biphenyl or multifunctional epoxy mold compounds. The following assumptions were used in calculating this table:

- 1. Activation Energy for diffusion = 0.35eV (smallest known value).
- 2. For ≤60% RH, use Diffusivity = 0.121exp ( -0.35eV/kT) mm2/s (this used smallest known Diffusivity @ 30°C).
- 3. For >60% RH, use Diffusivity = 1.320exp (-0.35eV/kT) mm2/s (this used largest known Diffusivity @ 30°C).

# Recommended Equivalent Total Floor Life (days) @ 20°C, 25°C & 30°C, 35°C

For ICs with Novolac, Biphenyl and Multifunctional Epoxies (Reflow at same temperature at which the component was classified) Maximum Percent Relative Humidity

Package Type and	Moisture	<b>E</b> 0/	400/	200/	200/	400/	<b>50</b> 0/	600/	700/	000/	000/	
Body Thickness Body Thickness ≥3.1 mm	Sensitivity Level Level 2a	5%	10% ∞	<b>20%</b> 94	<b>30</b> %	<b>40</b> %	<b>50</b> %	<b>60%</b>	<b>70</b> %	<b>80</b> %	<b>90</b> %	35°C
ncluding	Level 2a	∞ ∞	∞	124	60	41	33	28	10	7	6	30°C
PQFPs >84 pin,		∞	∞	167	78	53	42	36	14	10	8	25°C
PLCCs (square) All MQFPs or All BGAs ≥1 mm		∞	∞	231	103	69	57	47	19	13	10	20°C
	Level 3	∞	∞	8	7	6	6	6	4	3	3	35°C
		∞	∞	10	9	8	7	7	5	4	4	30°C
		∞	∞	13 17	11 14	10 13	9 12	9 12	7	6 8	5 7	25°C
	Level 4	∞ ∞	3	3	3	2	2	2	10 2	1	1	20°C
	Level 4	∞	5	4	4	4	3	3	3	2	2	30°C
		∞	6	5	5	5	5	4	3	3	3	25°C
		∞	8	7	7	7	7	6	5	4	4	20°C
	Level 5	∞	2	2	2	2	1	1	1	1	1	35°C
		∞	4	3	3	2	2	2	2	1	1	30°C
		∞ ∞	5 7	5 7	4 6	4 5	3 5	3 4	2 3	2 3	2 3	25°C 20°C
	Level 5a	∞	1	1	1	 1	 1	1	 1	1	 1	35°C
	Level Ja	∞	2	1	1	1	1	1	1	1	1	30°C
		∞	3	2	2	2	2	2	1	1	1	25°C
		∞	5	4	3	3	3	2	2	2	2	20°C
Body 2.1 mm	Level 2a	∞	∞	∞	∞	58	30	22	3	2	1	35°C
≤ Thickness		∞	∞	∞	∞	86	39	28	4	3	2	30°C
<3.1 mm including PLCCs (rectangular)		∞	∞ ∞	∞	∞	148 ∞	51 69	37 49	6 8	4 5	3 4	25°C 20°C
18-32 pin	Level 3	∞	∞ ∞	12	9	7	6	5	2	2	1	35°C
SOICs (wide body)	Level 3	∞	∞	19	12	9	8	7	3	2	2	30°C
SOICs ≥20 pins,		∞	∞	25	15	12	10	9	5	3	3	25°C
PQFPs ≤80 pins		∞	∞	32	19	15	13	12	7	5	4	20°C
	Level 4	∞	5	4	3	3	2	2	1	1	1	35°C
		∞	7	5	4	4	3	3	2	2	1	30°C
		∞	9 11	7 9	5 7	5 6	4 6	4 5	3 4	2 3	2 3	25°C 20°C
	Level 5	∞	3	2	2	2	2	 1	1	1	 1	35°C
	Level 5	∞	4	3	3	2	2	2	1	1	1	30°C
		∞	5	4	3	3	3	3	2	1	1	25°C
		∞	6	5	5	4	4	4	3	3	2	20°C
	Level 5a	∞	1	1	1	1	1	1	1	0.5	0.5	35°C
		∞	2	1	1	1	1	1	1	0.5	0.5	30°C
		∞ ∞	2	2 2	2 2	2 2	2 2	2 2	1 2	1 2	1 1	25°C 20°C
Body Thickness < 2.1 mm	Level 2a	∞ ∞	∞	∞	∞	∞	∞	17	1	0.5	0.5	35°C
including	Level 2a	∞	∞	∞	∞	∞	∞	28	1	1	1	30°C
SOICs < 18 pin All TQFPs, TSOPs or All BGAs < 1 mm body		∞	∞	∞	∞	∞	∞	∞	2	1	1	25°C
		∞	∞	∞	∞	∞	∞	∞	2	2	1	20°C
	Level 3	∞	∞	∞	∞	∞	8	5	1	0.5	0.5	35°C
		∞	∞	∞	∞	∞	11	7 10	1	1	1	30°C
thickness		∞	∞ ∞	∞	∞	∞ ∞	14 20	13	2 2	1 2	1 1	25°C 20°C
	Level 4	∞	∞	∞	7	4	3	2	1	0.5	0.5	35°C
	20.0.1	∞	∞	∞	9	5	4	3	1	1	1	30°C
		∞	∞	∞	12	7	5	4	2	1	1	25°C
		∞	∞	∞	17	9	7	6	2	2	1	20°C
	Level 5	∞	∞	7	3	2	2	1	1	0.5	0.5	35°C
		∞	∞	13	5	3	2	2	1	1	1	30°C
		∞	∞	18 26	6 8	4 6	3 5	3 4	2 2	1 2	1 1	25°0 20°0
	Level 5a	∞ ∞		20	1	1	 1	1	1	0.5	0.5	35°C
	Level Ja	∞	10	3	2	1	1	1	1	1	0.5	30°C
		∞	13	5	3	2	2	2	1	1	1	25°C
		∞	18	6	4	3	2	2	2	2	1	20°0

For product information and a complete list of distributors, please go to our web site: **www.avagotech.com** 

